

---

# DIC L17: Delay (5)

Sung-Min Hong ([smhong@gist.ac.kr](mailto:smhong@gist.ac.kr))

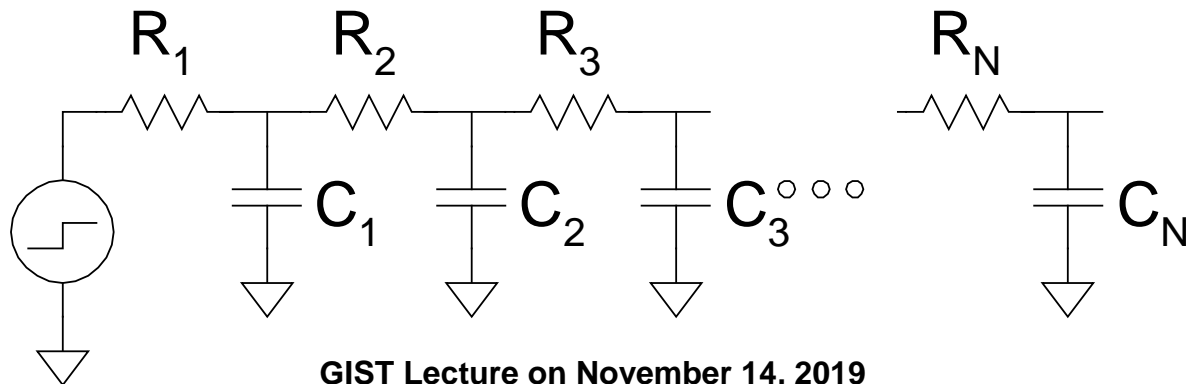
Semiconductor Device Simulation Lab.  
School of Electrical Engineering and Computer Science  
Gwangju Institute of Science and Technology

## 4.3. RC delay model (7)

- Example 4.4
  - A simple single time constant approximation

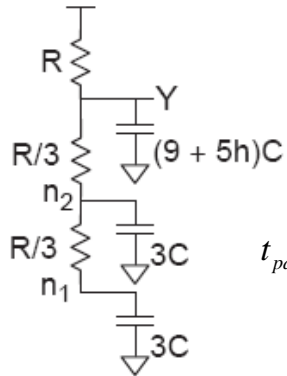
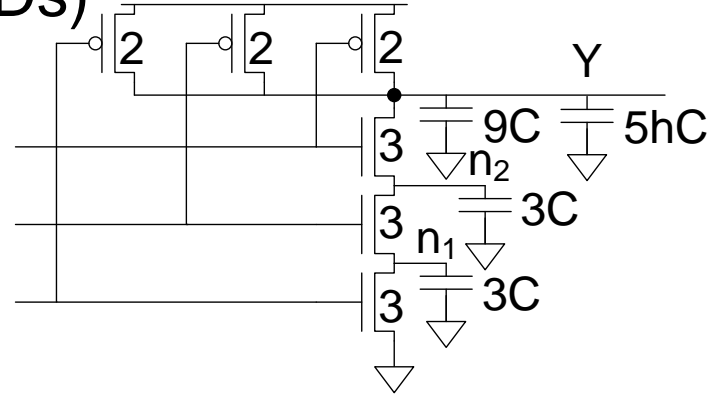
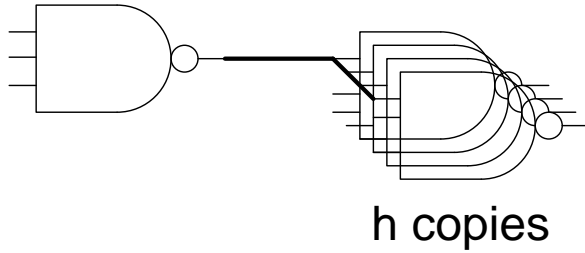
$$t_{pd} \approx \sum_{\text{nodes } i} R_{i-to-source} C_i \quad \text{Eq. (4.14)}$$

$$= R_1 C_1 + (R_1 + R_2) C_2 + \dots + (R_1 + R_2 + \dots + R_N) C_N$$

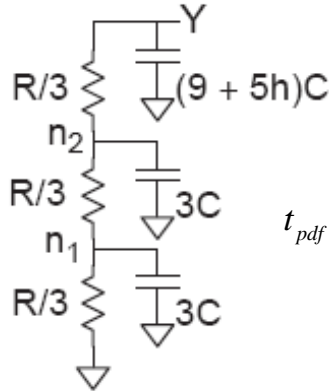


# 4.3. RC delay model (8)

- Example 4.7 ( $h$  identical NANDs)



$$t_{pdr} = (9 + 5h)RC$$



$$\begin{aligned} t_{pdf} &= (3C)\left(\frac{R}{3}\right) + (3C)\left(\frac{R}{3} + \frac{R}{3}\right) + [(9 + 5h)C]\left(\frac{R}{3} + \frac{R}{3} + \frac{R}{3}\right) \\ &= (12 + 5h)RC \end{aligned}$$

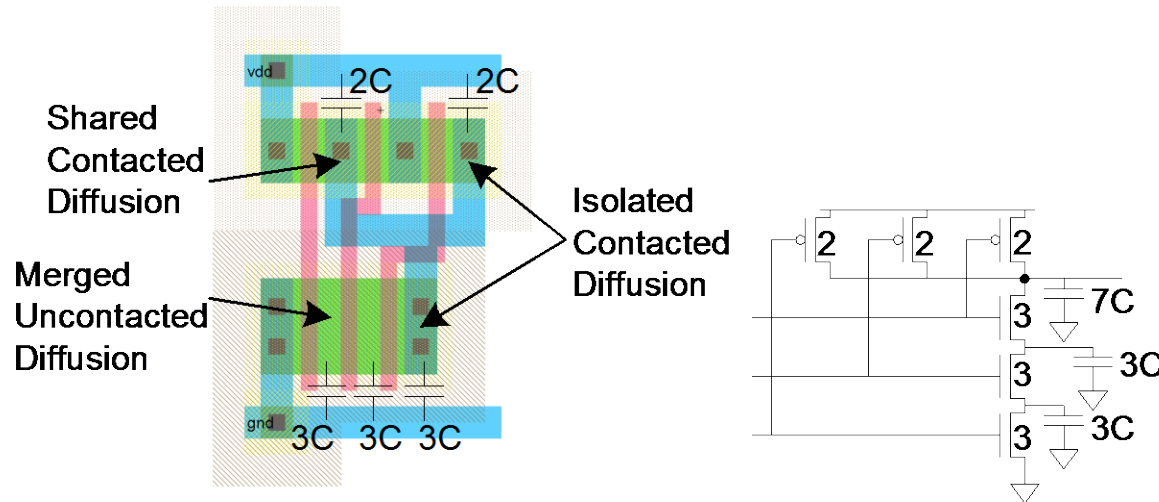
## 4.3. RC delay model (9)

---

- Delay components
  - Parasitic delay
    - 9 or 12 RC
    - Independent on load
  - Effort delay
    - $5h$  RC
    - Proportional to load capacitance

## 4.3. RC delay model (9)

- Layout dependence of capacitance
  - Good layout minimizes the diffusion area.



## 4.4. Linear delay model (1)

---

- Delay in a logic gate
  - Express delays in process-independent unit

$$d = \frac{t_{pd}}{\tau} = \frac{t_{pd}}{3RC} \quad \text{Eq. (4.15)}$$

- Delay has two components:

$$d = f + p \quad \text{Eq. (4.20)}$$

- Effort delay

$$f = gh \quad \text{Eq. (4.21)}$$

- Logical effort,  $g$ 
    - $g \equiv 1$  for inverter

## 4.4. Linear delay model (2)

---

- Delay in a logic gate (continued)

- Electrical effort

$$h = \frac{C_{out}}{C_{in}} \quad \text{Eq. (4.22)}$$

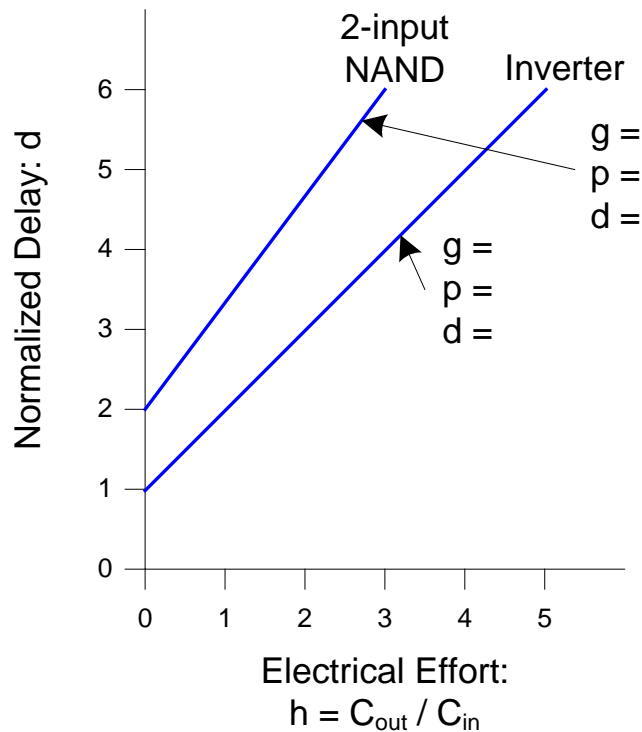
- Ratio of output to input capacitance

- Parasitic delay,  $p$

- Represents delay of gate driving no load
    - Set by internal parasitic capacitance

## 4.4. Linear delay model (3)

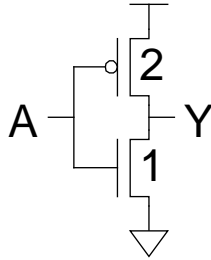
- Normalized delay versus fanout



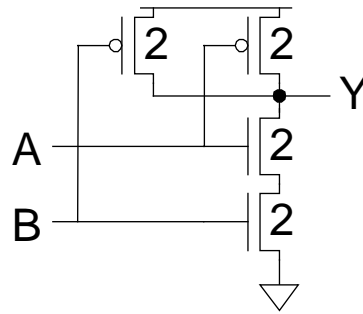


# 4.4. Linear delay model (4)

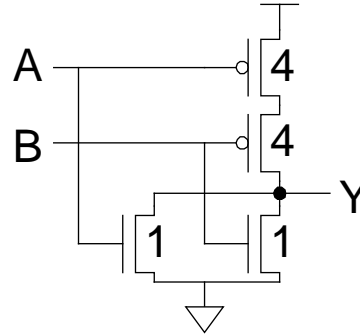
- Computing logical effort
  - *Logical effort is the ratio of the input capacitance of a gate to the input capacitance of an inverter delivering the same output current.*



$$C_{in} = 3$$
$$g = 3/3$$



$$C_{in} = 4$$
$$g = 4/3$$



$$C_{in} = 5$$
$$g = 5/3$$

## 4.4. Linear delay model (5)

---

- Logical effort of common gates

Gate type	Number of inputs				
	1	2	3	4	n
Inverter	1				
NAND		$4/3$	$5/3$	$6/3$	$(n+2)/3$
NOR		$5/3$	$7/3$	$9/3$	$(2n+1)/3$
Tristate / mux	2	2	2	2	2
XOR, XNOR		4, 4	6, 12, 6	8, 16, 16, 8	

## 4.4. Linear delay model (6)

---

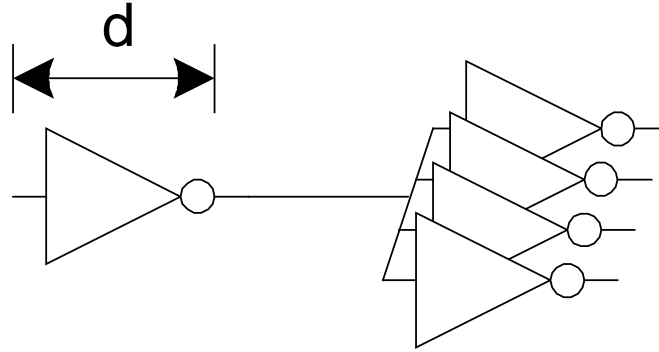
- Parasitic delay of common gates

Gate type	Number of inputs				
	1	2	3	4	n
Inverter	1				
NAND		2	3	4	n
NOR		2	3	4	n
Tristate / mux	2	4	6	8	2n
XOR, XNOR		4	6	8	

## 4.4. Linear delay model (7)

---

- Example 4.10

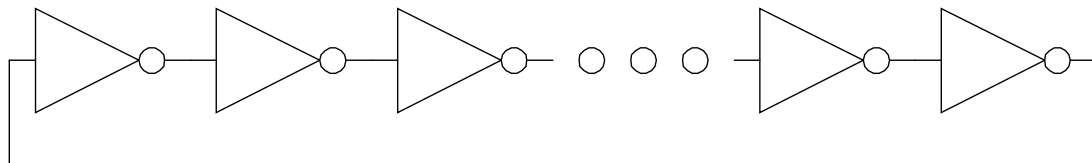


- Logical Effort:  $g = 1$
- Electrical Effort:  $h = 4$
- Parasitic Delay:  $p = 1$
- Stage Delay:  $d = 5$
- When  $\tau = 3RC = 3 \text{ ps}$ , the total delay is 15 ps.

## 4.4. Linear delay model (8)

---

- Example 4.11



- Logical Effort:  $g = 1$
- Electrical Effort:  $h = 1$
- Parasitic Delay:  $p = 1$
- Stage Delay:  $d = 2$
- Frequency:  $f_{\text{osc}} = 1/(2 \cdot N \cdot d) = 1/4N$